

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ P6

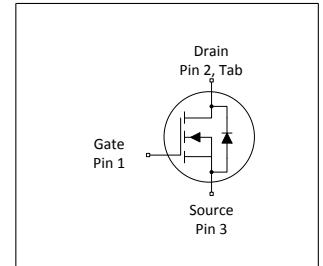
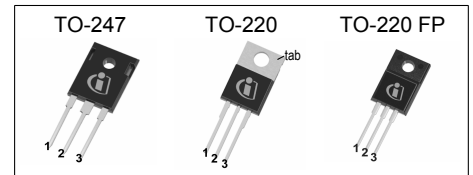
600V CoolMOS™ P6 Power Transistor
IPx60R125P6

Data Sheet

Rev. 2.0
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ P6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.



Features

- Increased MOSFET dv/dt ruggedness
- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)



Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.



Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|----------------------|-------|------|
| $V_{DS} @ T_{j,max}$ | 650 | V |
| $R_{DS(on),max}$ | 125 | mΩ |
| $Q_{g,typ}$ | 56 | nC |
| $I_{D,pulse}$ | 87 | A |
| $E_{oss@400V}$ | 7.2 | μJ |
| Body diode di/dt | 300 | A/μs |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|-------------------|---------|----------------|
| IPW60R125P6 | PG-TO 247 | 6R125P6 | see Appendix A |
| IPP60R125P6 | PG-TO 220 | | |
| IPA60R125P6 | PG-TO 220 FullPAK | | |



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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---------------|--------|------|--------------|------------------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | - | - | 30.0 19.0 | A | $T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 87 | A | $T_C=25^\circ\text{C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 636 | mJ | $I_D=5.2\text{A}$; $V_{DD}=50\text{V}$; see table 10 |
| Avalanche energy, repetitive | E_{AR} | - | - | 0.96 | mJ | $I_D=5.2\text{A}$; $V_{DD}=50\text{V}$; see table 10 |
| Avalanche current, repetitive | I_{AR} | - | - | 5.2 | A | - |
| MOSFET dv/dt ruggedness | dv/dt | - | - | 100 | V/ns | $V_{DS}=0\dots400\text{V}$ |
| Gate source voltage (static) | V_{GS} | -20 | - | 20 | V | static; |
| Gate source voltage (dynamic) | V_{GS} | -30 | - | 30 | V | AC ($f>1\text{ Hz}$) |
| Power dissipation (Non FullPAK) TO-220, TO-247 | P_{tot} | - | - | 219 | W | $T_C=25^\circ\text{C}$ |
| Power dissipation (FullPAK) TO-220FP | P_{tot} | - | - | 34 | W | $T_C=25^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 | - | 150 | $^\circ\text{C}$ | - |
| Operating junction temperature | T_j | -55 | - | 150 | $^\circ\text{C}$ | - |
| Mounting torque (Non FullPAK) TO-220, TO-247 | - | - | - | 60 | Ncm | M3 and M3.5 screws |
| Mounting torque (FullPAK) TO-220FP | - | - | - | 50 | Ncm | M2.5 screws |
| Continuous diode forward current | I_S | - | - | 26.0 | A | $T_C=25^\circ\text{C}$ |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | - | - | 87 | A | $T_C=25^\circ\text{C}$ |
| Reverse diode dv/dt ³⁾ | dv/dt | - | - | 15 | V/ns | $V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8 |
| Maximum diode commutation speed | di/dt | - | - | 300 | A/ μs | $V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8 |
| Insulation withstand voltage for TO-220FP | V_{ISO} | - | - | 2500 | V | V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$ |

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics (Non FullPAK) TO-220, TO-247

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|-------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 0.57 | °C/W | - |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 62 | °C/W | leaded |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | °C | 1.6mm (0.063 in.) from case for 10s |

Table 4 Thermal characteristics (FullPAK) TO-220FP

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|-------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3.65 | °C/W | - |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 80 | °C/W | leaded |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | °C | 1.6mm (0.063 in.) from case for 10s |

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 5 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|----------------|-------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 600 | - | - | V | $V_{GS}=0\text{V}$, $I_D=1\text{mA}$ |
| Gate threshold voltage | $V_{(GS)th}$ | 3.5 | 4.0 | 4.5 | V | $V_{DS}=V_{GS}$, $I_D=0.96\text{mA}$ |
| Zero gate voltage drain current | I_{DSS} | - | - | 2 | μA | $V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$ $V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=150^\circ\text{C}$ |
| Gate-source leakage current | I_{GSS} | - | - | 100 | nA | $V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 0.113 0.293 | 0.125 | Ω | $V_{GS}=10\text{V}$, $I_D=11.6\text{A}$, $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$, $I_D=11.6\text{A}$, $T_j=150^\circ\text{C}$ |
| Gate resistance | R_G | - | 1.7 | - | Ω | $f=1\text{MHz}$, open drain |

Table 6 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | - | 2660 | - | pF | $V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $f=1\text{MHz}$ |
| Output capacitance | C_{oss} | - | 110 | - | pF | $V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $f=1\text{MHz}$ |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | - | 90 | - | pF | $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$ |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | - | 398 | - | pF | $I_D=\text{constant}$, $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$ |
| Turn-on delay time | $t_{d(on)}$ | - | 14 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=14.5\text{A}$, $R_G=1.7\Omega$; see table 9 |
| Rise time | t_r | - | 9 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=14.5\text{A}$, $R_G=1.7\Omega$; see table 9 |
| Turn-off delay time | $t_{d(off)}$ | - | 44 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=14.5\text{A}$, $R_G=1.7\Omega$; see table 9 |
| Fall time | t_f | - | 5 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=14.5\text{A}$, $R_G=1.7\Omega$; see table 9 |

Table 7 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 16 | - | nC | $V_{DD}=400\text{V}$, $I_D=14.5\text{A}$, $V_{GS}=0$ to 10V |
| Gate to drain charge | Q_{gd} | - | 20 | - | nC | $V_{DD}=400\text{V}$, $I_D=14.5\text{A}$, $V_{GS}=0$ to 10V |
| Gate charge total | Q_g | - | 56 | - | nC | $V_{DD}=400\text{V}$, $I_D=14.5\text{A}$, $V_{GS}=0$ to 10V |
| Gate plateau voltage | $V_{plateau}$ | - | 6.1 | - | V | $V_{DD}=400\text{V}$, $I_D=14.5\text{A}$, $V_{GS}=0$ to 10V |

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 8 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------|---|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | - | 0.9 | - | V | $V_{GS}=0V, I_F=14.5A, T_j=25^{\circ}C$ |
| Reverse recovery time | t_{rr} | - | 385 | - | ns | $V_R=400V, I_F=14.5A, di_F/dt=100A/\mu s$; see table 8 |
| Reverse recovery charge | Q_{rr} | - | 7 | - | μC | $V_R=400V, I_F=14.5A, di_F/dt=100A/\mu s$; see table 8 |
| Peak reverse recovery current | I_{rrm} | - | 32 | - | A | $V_R=400V, I_F=14.5A, di_F/dt=100A/\mu s$; see table 8 |

5 Electrical characteristics diagrams

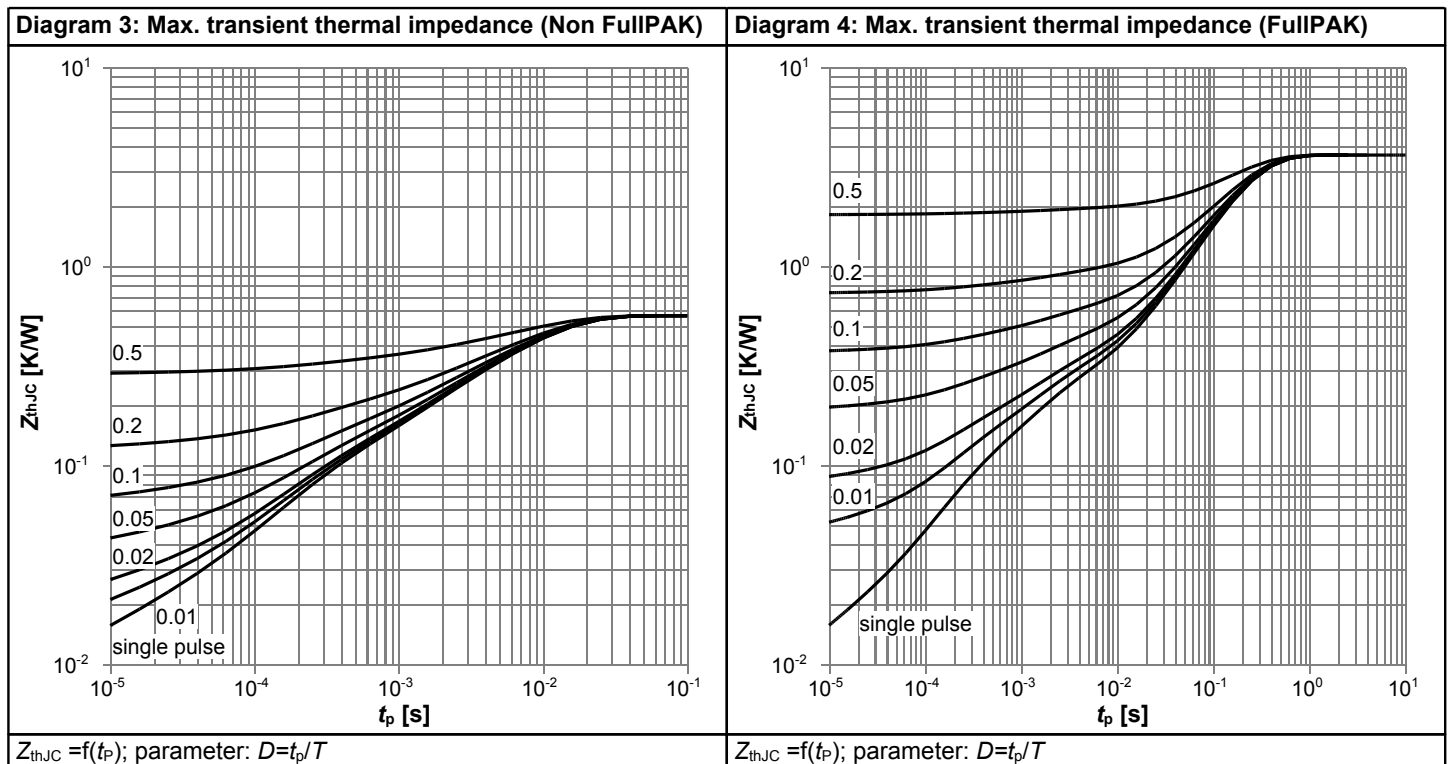
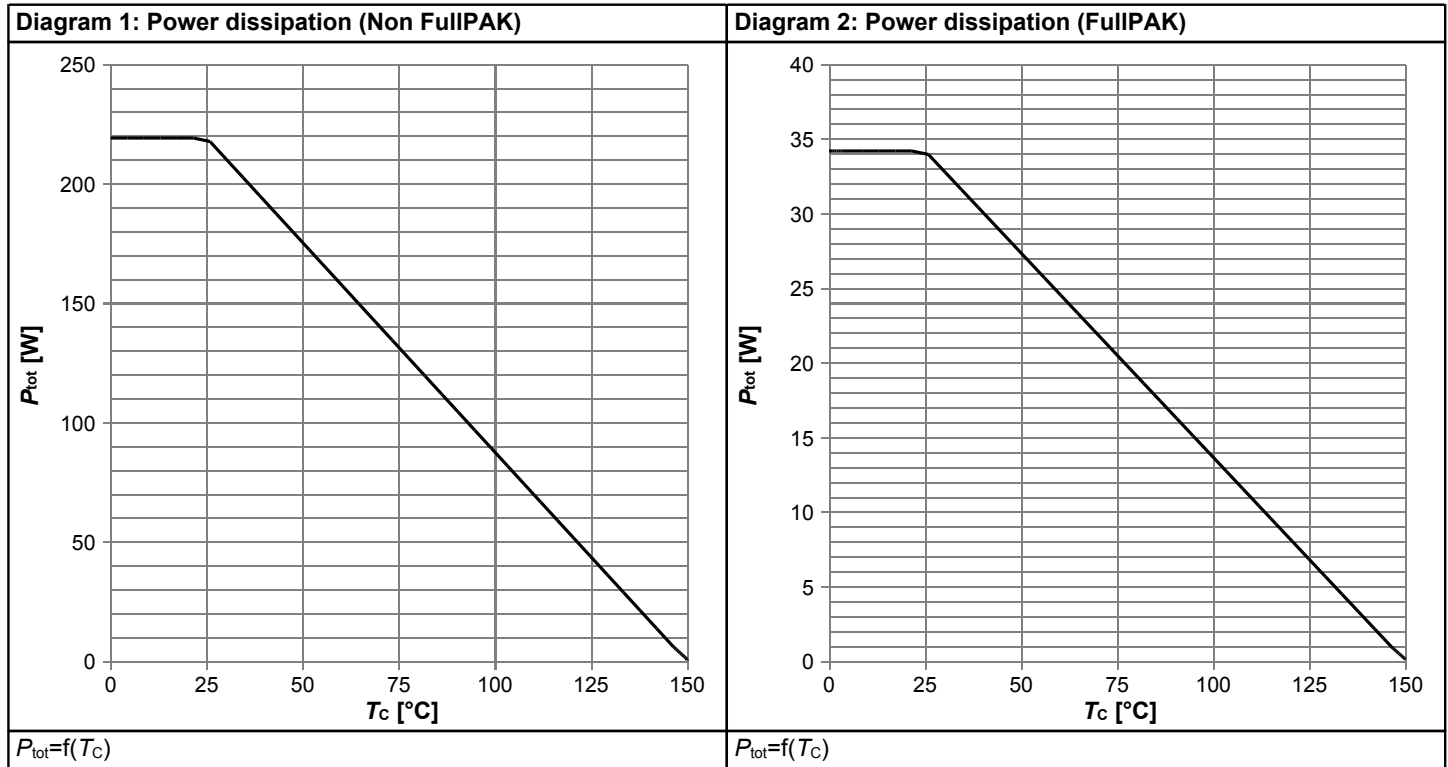
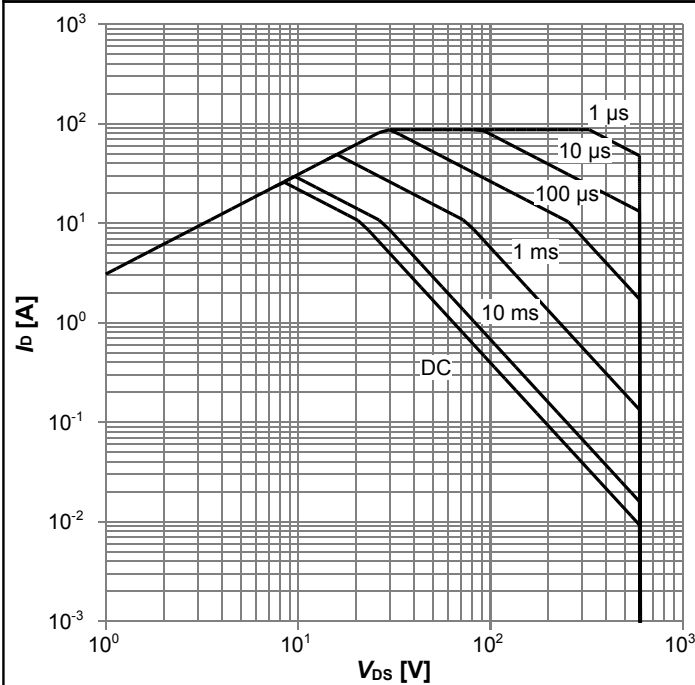
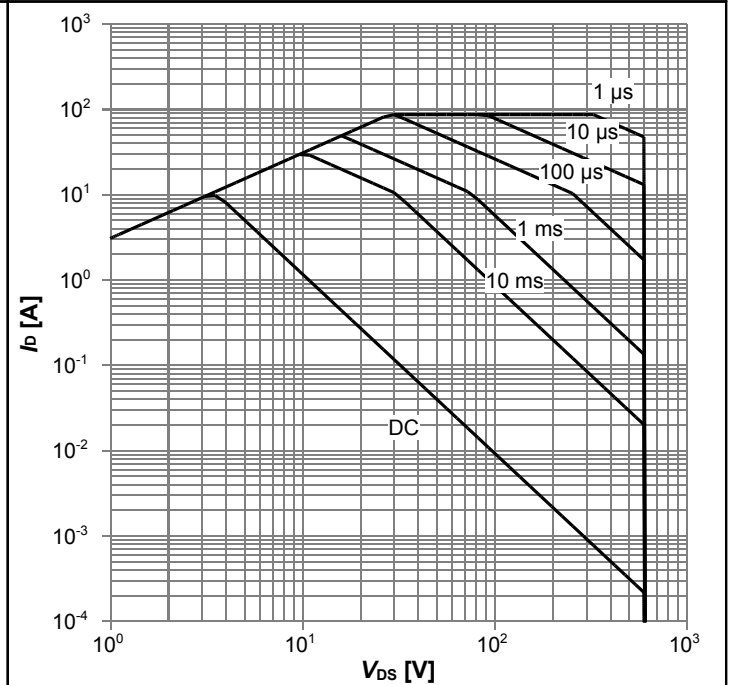


Diagram 5: Safe operating area (Non FullPAK)



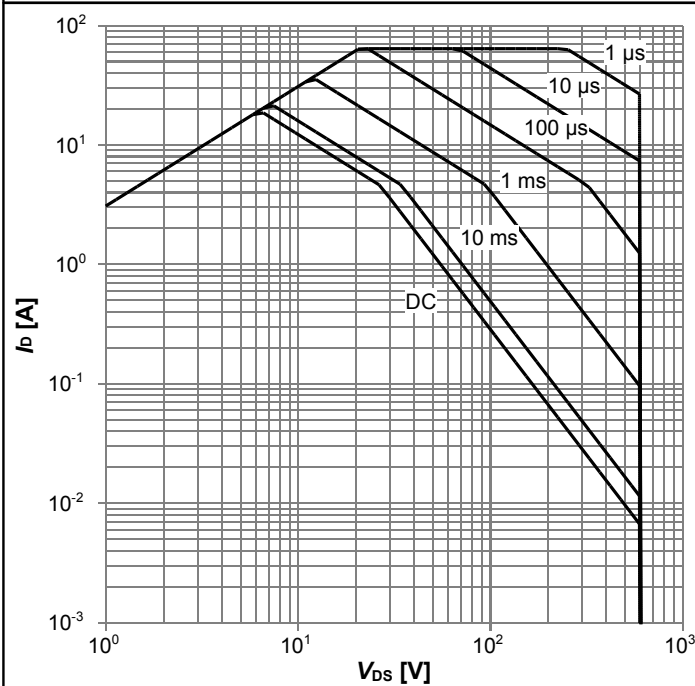
$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$; parameter: t_p

Diagram 6: Safe operating area (FullPAK)



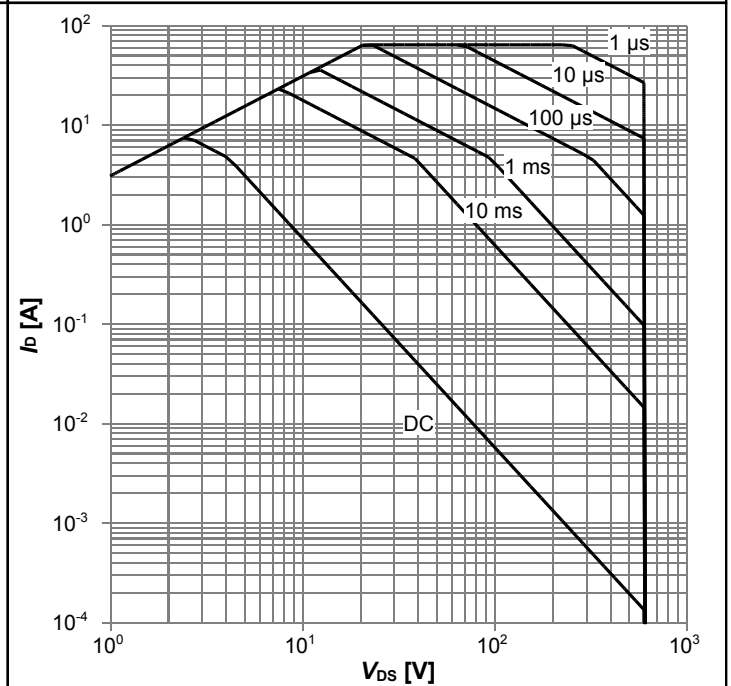
$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$; parameter: t_p

Diagram 7: Safe operating area (Non FullPAK)



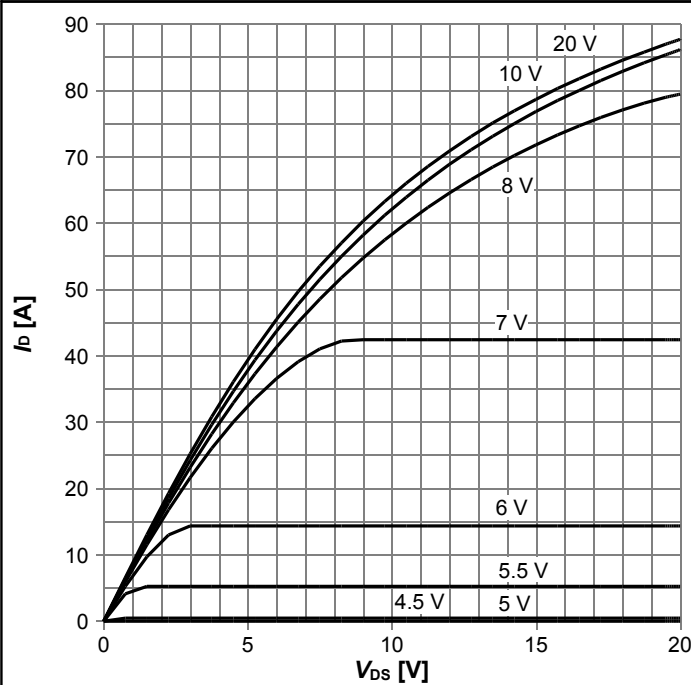
$I_D=f(V_{DS}); T_C=80\text{ °C}; D=0$; parameter: t_p

Diagram 8: Safe operating area (FullPAK)



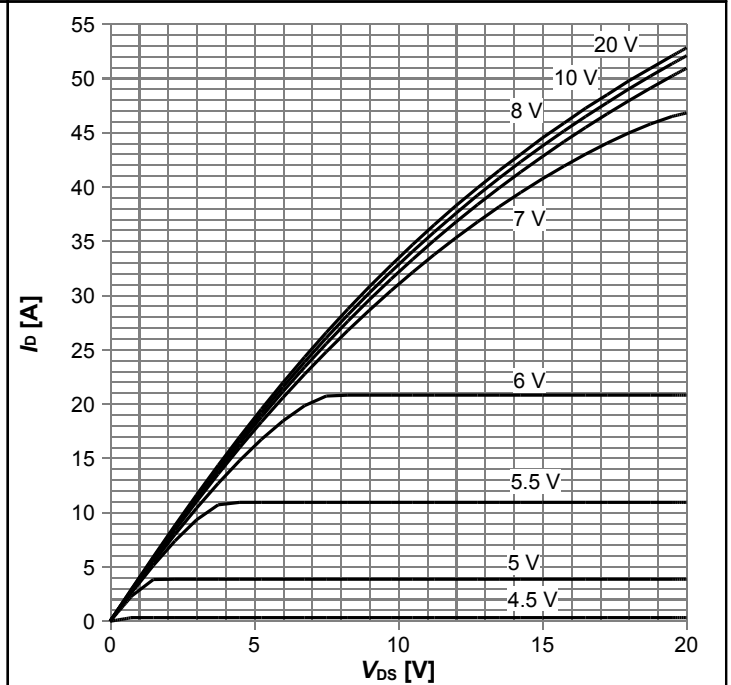
$I_D=f(V_{DS}); T_C=80\text{ °C}; D=0$; parameter: t_p

Diagram 9: Typ. output characteristics



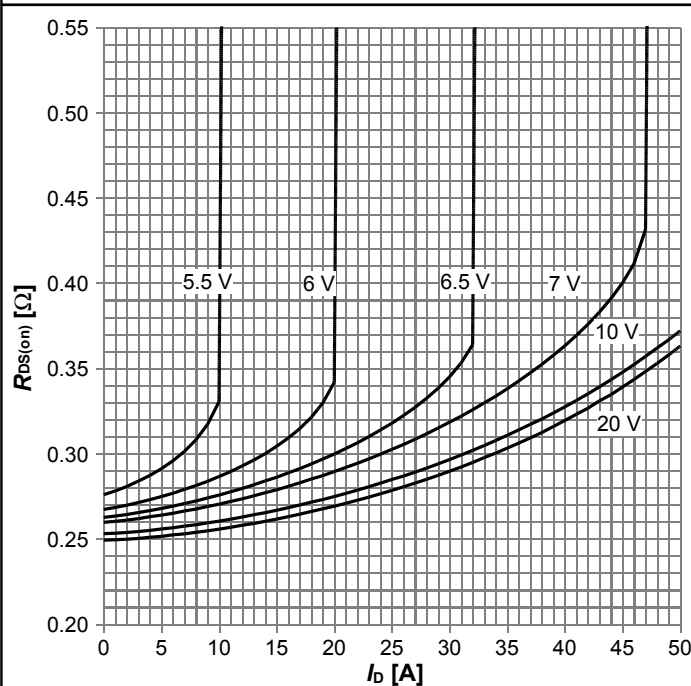
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 10: Typ. output characteristics



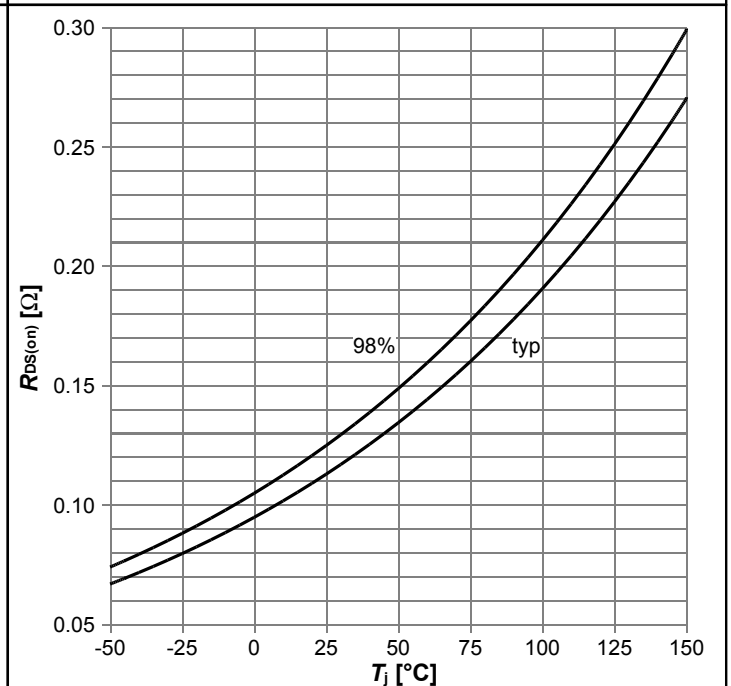
$I_D = f(V_{DS})$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 11: Typ. drain-source on-state resistance



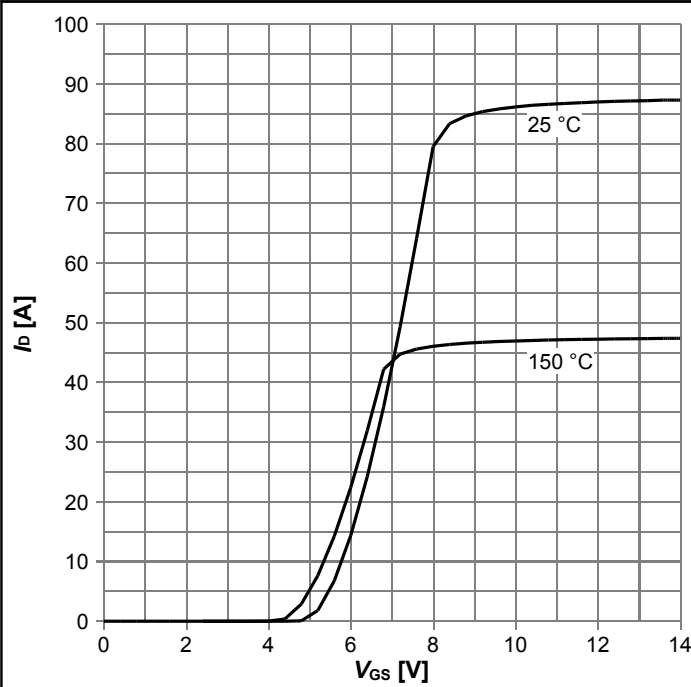
$R_{DS(on)} = f(I_D)$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 12: Drain-source on-state resistance



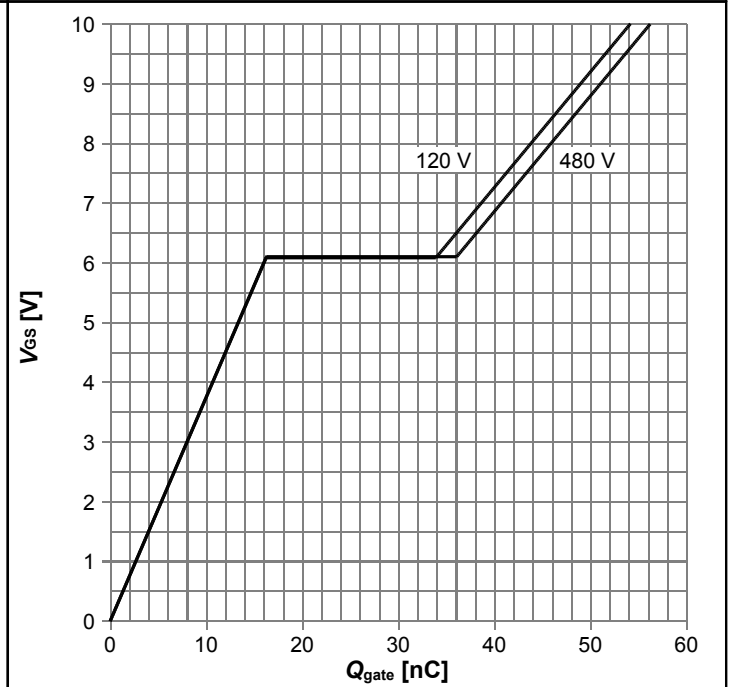
$R_{DS(on)} = f(T_j)$; $I_D = 11.6\text{ A}$; $V_{GS} = 10\text{ V}$

Diagram 13: Typ. transfer characteristics



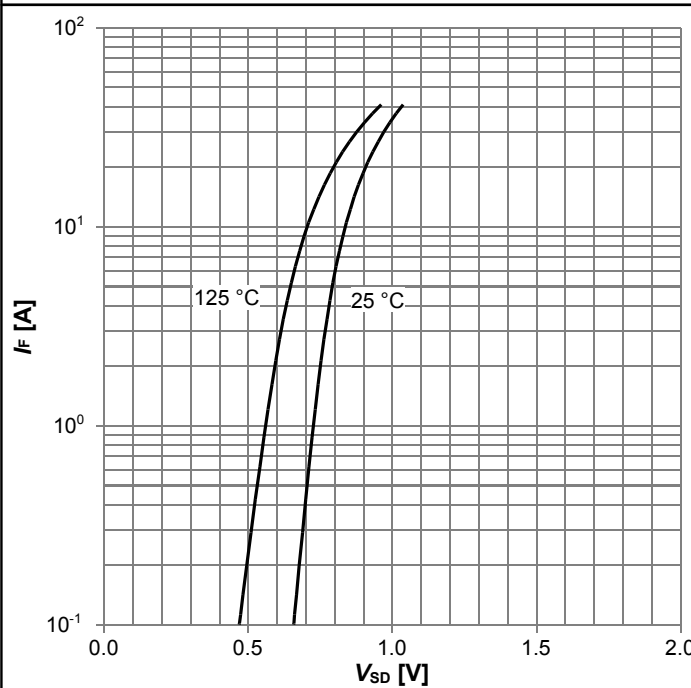
$I_D=f(V_{GS}); V_{DS}=20V; \text{parameter: } T_j$

Diagram 14: Typ. gate charge



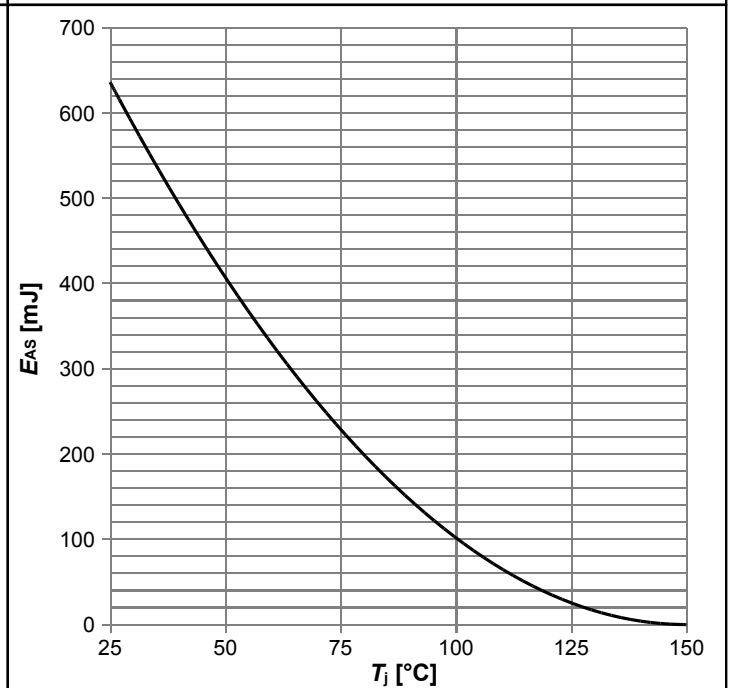
$V_{GS}=f(Q_{\text{gate}}); I_D=14.5 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 15: Forward characteristics of reverse diode



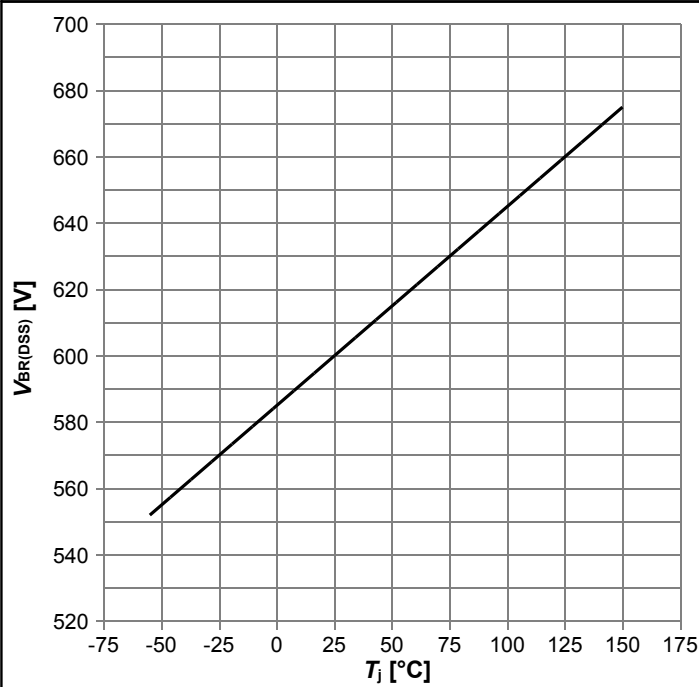
$I_F=f(V_{SD}); \text{parameter: } T_j$

Diagram 16: Avalanche energy



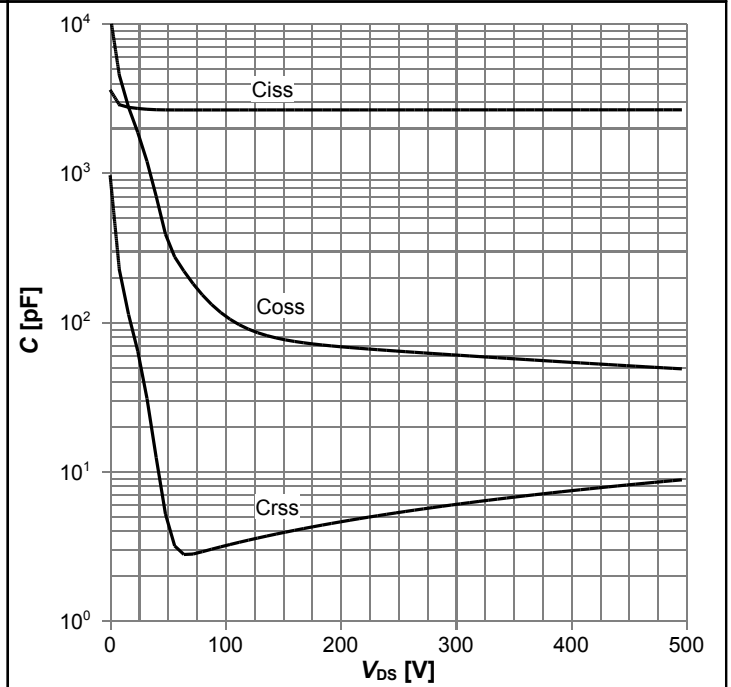
$E_{AS}=f(T_j); I_D=5.2 \text{ A}; V_{DD}=50 \text{ V}$

Diagram 17: Drain-source breakdown voltage



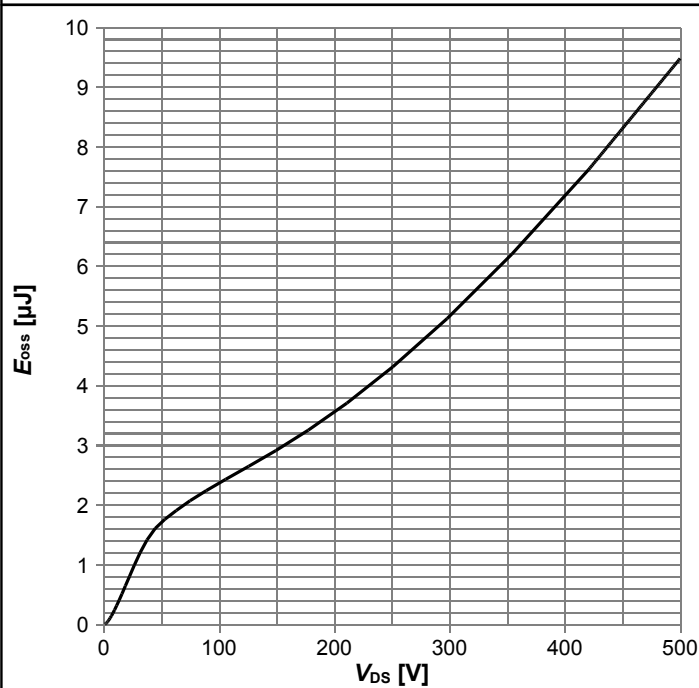
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram 18: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=1 \text{ MHz}$

Diagram 19: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

6 Test Circuits

Table 9 Diode characteristics

| Test circuit for diode characteristics | Diode recovery waveform |
|--|---|
| <p>$R_{g1} = R_{g2}$</p> | <p>$t_{tr} = t_F + t_S$ $Q_{rr} = Q_F + Q_S$</p> |

Table 10 Switching times

| Switching times test circuit for inductive load | Switching times waveform |
|---|--------------------------|
| | |

Table 11 Unclamped inductive load

| Unclamped inductive load test circuit | Unclamped inductive waveform |
|---------------------------------------|------------------------------|
| | |

7 Package Outlines

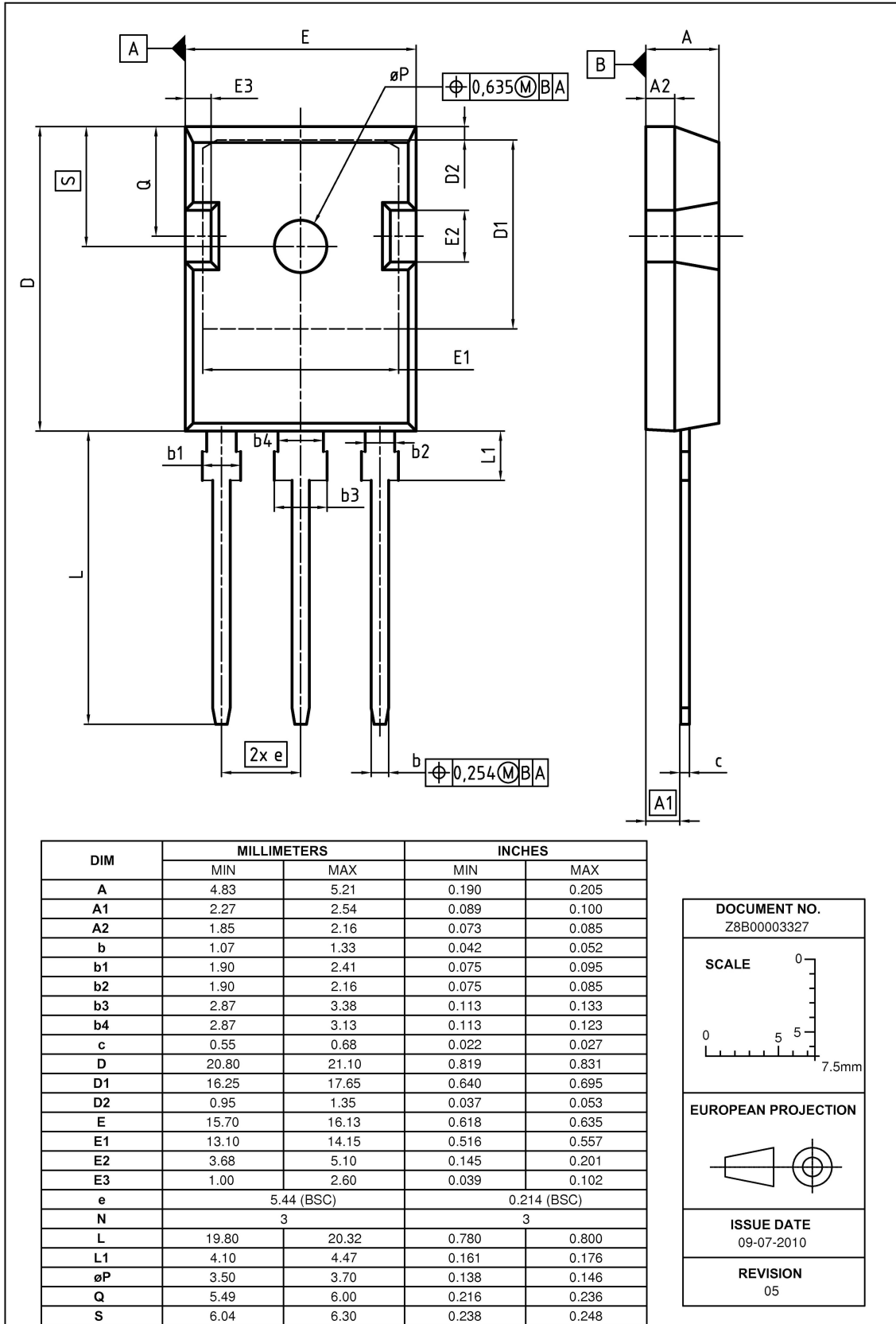


Figure 1 Outline PG-TO 247, dimensions in mm/inches

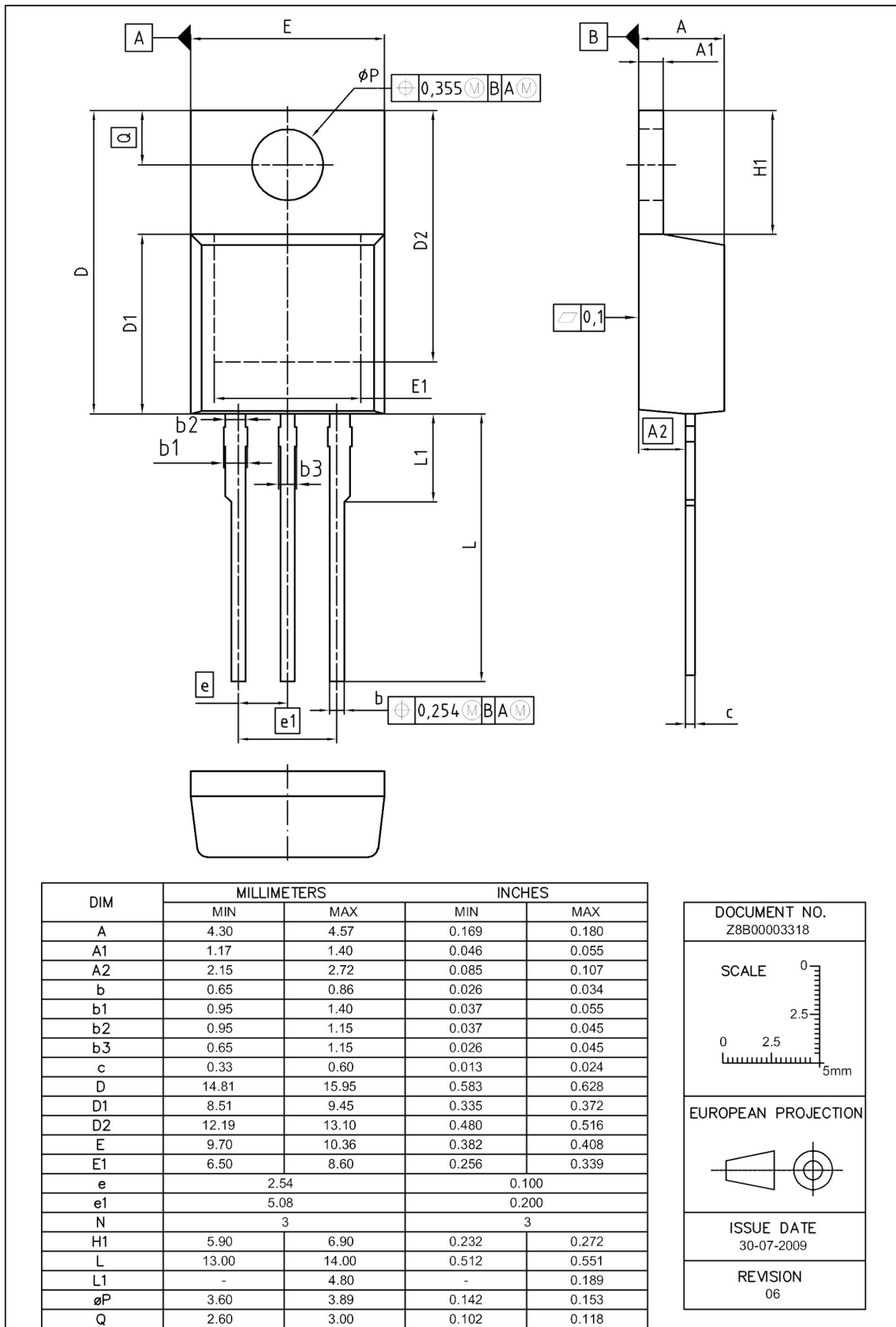


Figure 2 Outline PG-TO 220, dimensions in mm/inches

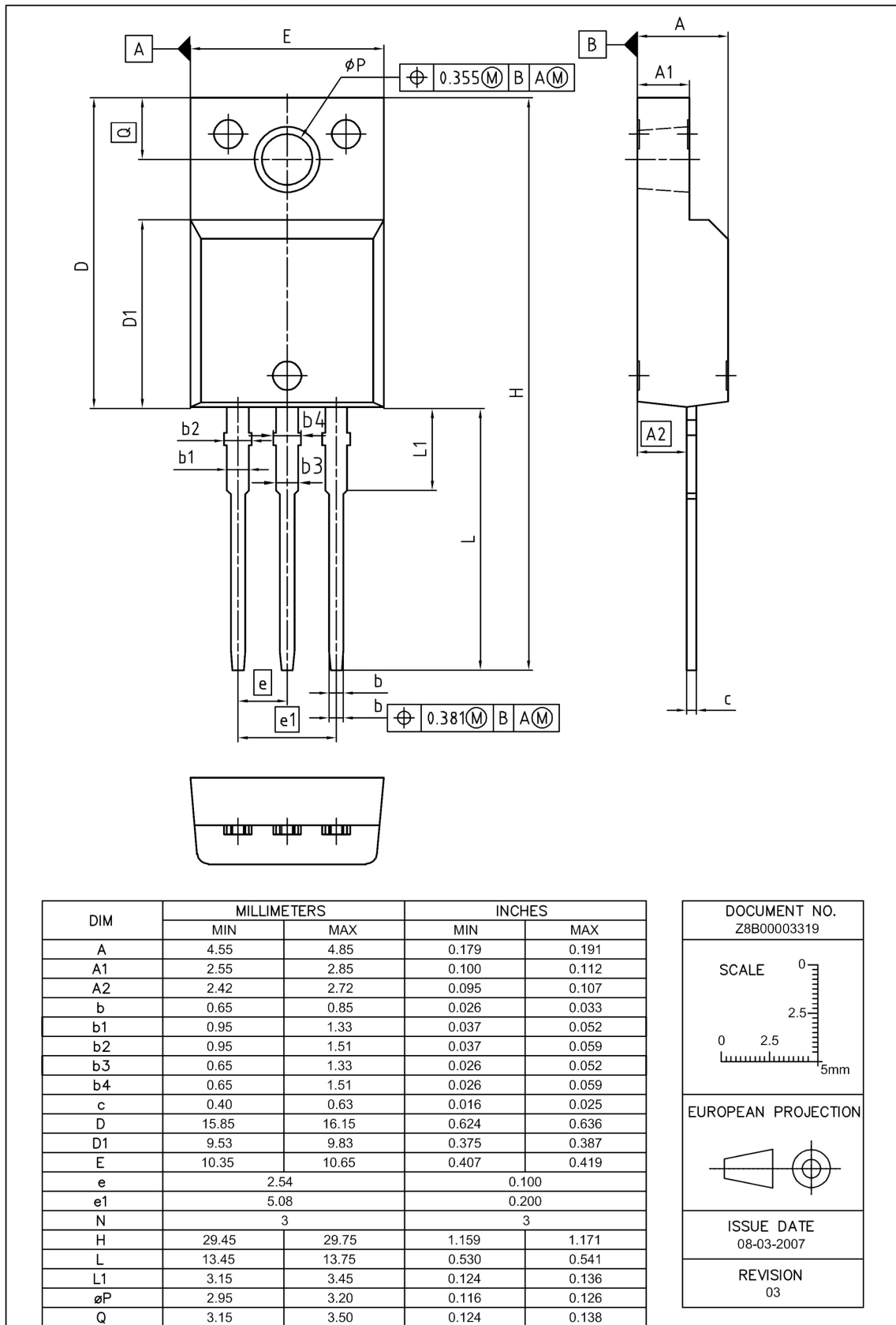


Figure 3 Outline PG-TO 220 FullPAK, dimensions in mm/inches

8 Appendix A

Table 12 Related Links

- IFX CoolMOS™ P6 Webpage: www.infineon.com
- IFX CoolMOS™ P6 application note: www.infineon.com
- IFX CoolMOS™ P6 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPW60R125P6, IPP60R125P6, IPA60R125P6

Revision: 2014-03-07, Rev. 2.0

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0 | 2014-03-07 | Release of final version |

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